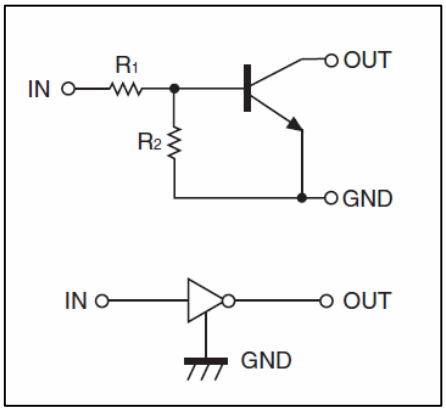
Digital Transistors (Built-in Resistors)

DIGITAL TRANSISTOR (NPN)

• **Equivalent Circuit**



FEATURES

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors(see equivalent circuit)
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input.They also have the advantage of almost completely eliminating parasitic effects
- Only the on/off conditions need to be set for operation, making device design easy

MARKING: 22

Absolute Maximum Ratings (T_a = 25℃)

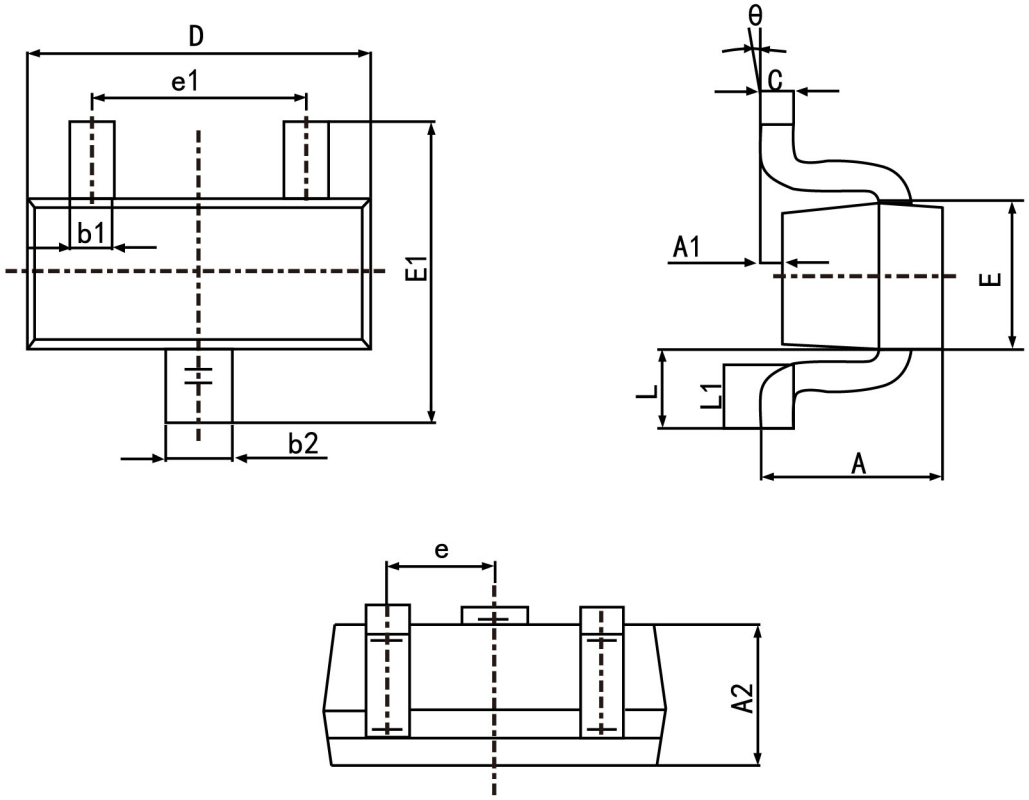
Parameter	Symbol	Value	Unit
Collector Emitter Voltage	V_{CEO}	50	V
Input Voltage	V_I	- 10 to + 40	V
Collector Current	I_C	100	mA
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	- 55 to + 150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input voltage	$V_{I(off)}$	V_{CC}=5V,I_O=100μA	0.5			V
	$V_{I(on)}$	V_O=0.3V,I_O=20mA			3	V
Output voltage	$V_{O(on)}$	I_O/I_I=10mA/0.5mA			0.3	V
Input current	I_I	V_I=5V			3.8	mA
Output current	$I_{O(off)}$	V_{CC}=50V,V_I=0			0.5	μA
DC current gain	G_I	V_O=5V,I_O=20mA	20			
Input resistance	R_1		1.54	2.2	2.86	kΩ
Resistance ratio	R_2/R_1		0.8	1	1.2	
Transition frequency	f_T	V_O=10V,I_O=5mA,f=100MHz		250		MHz

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT-523**



Symbol	Dimension in Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
c	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500	TYP.
e1	0.900	1.100
L	0.400 REF.	
L1	0.260	0.460
θ	0°	8°